

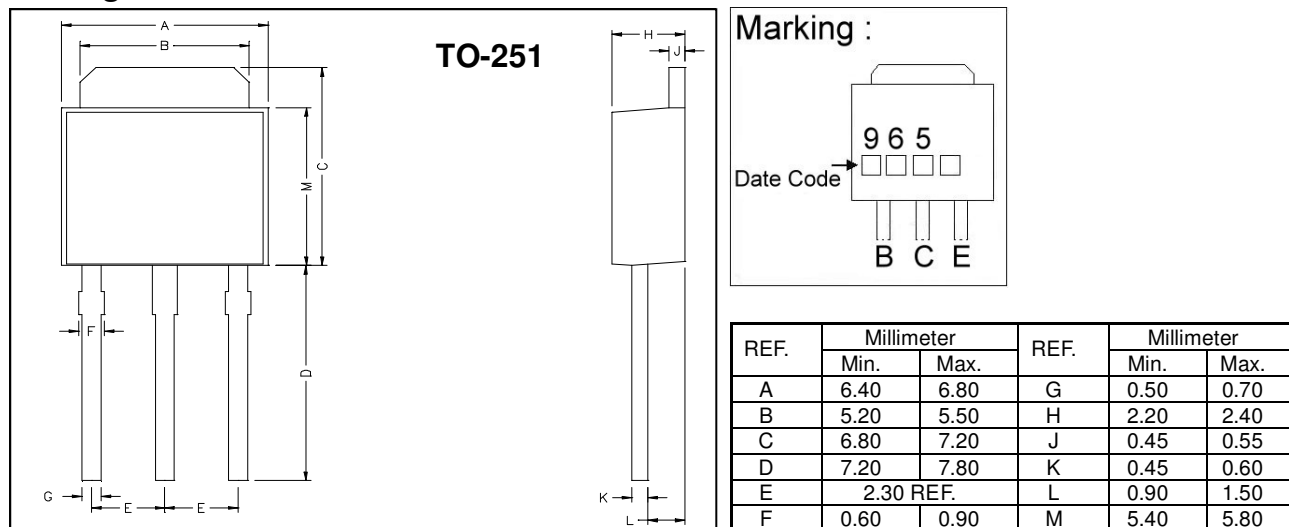
GI965

NPN EPITAXIAL PLANAR TRANSISTOR

Description

The GI965 is designed for use as AF output amplifier and flash unit.

Package Dimensions



Absolute Maximum Ratings (Ta = 25°C, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	VCBO	40	V
Collector to Emitter Voltage	VCEO	20	V
Emitter to Base Voltage	VEBO	7	V
Collector Current (Continuous)	IC	5	A
Collector Current (Peak PT=10mS)	ICP	8	A
Junction Temperature	Tj	+150	°C
Storage Temperature	TSTG	-55 ~ +150	°C
Total Power Dissipation	Pd	2	W

Electrical Characteristics (Rating at Ta=25°C)

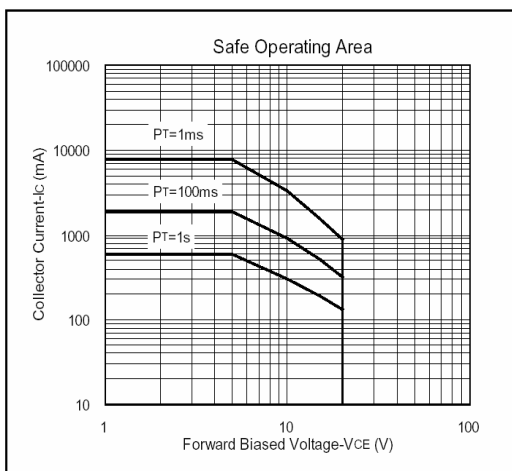
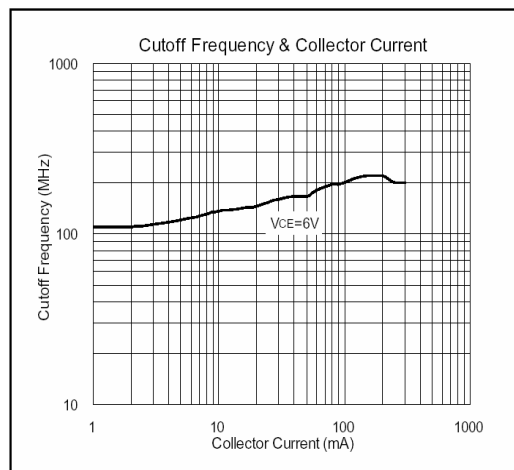
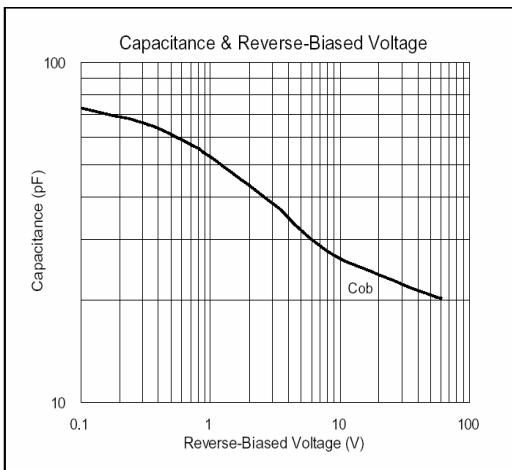
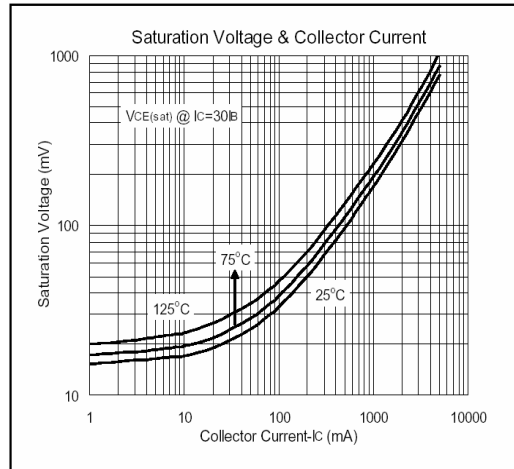
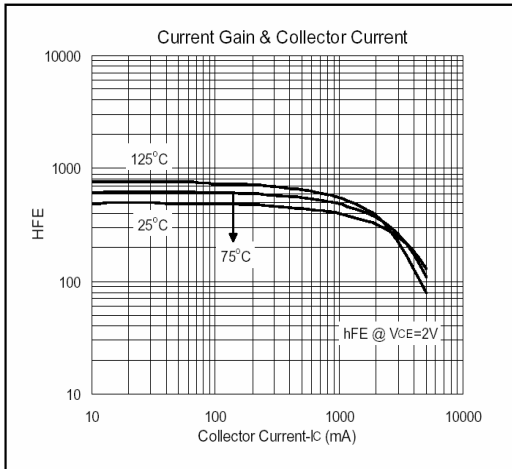
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	40	-	-	V	IC=100uA
BVCEO	20	-	-	V	IC=1mA
BVEBO	7	-	-	V	IE=10uA
ICBO	-	-	100	nA	VCB=60V
IEBO	-	-	100	nA	VEB=7V
*VCE(sat)	-	350	1000	mV	IC=3A, IB=100mA
*hFE1	230	-	800		VCE=2V, IC=500mA
*hFE2	150	-	-		VCE=2V, IC=2A
fT	-	150	-	MHz	VCE=6V, IE=50mA
Cob	-	-	50	pF	VCB=20V, f=1MHz

* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Classification Of hFE1

Rank	Q	R	S
Range	230 ~ 380	340 ~ 600	560 ~ 800

Characteristics Curve



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